

Development of Readout ASIC for FPCCD Vertex Detector at the ILC

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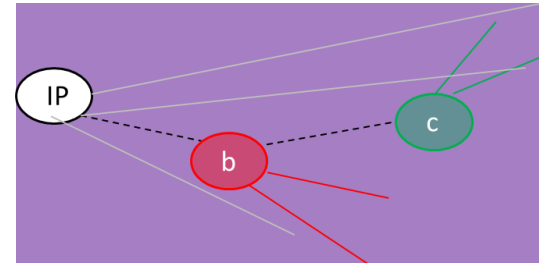
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A. Dubey, A. Ishikawa, T. Saito, Y. Sugimoto, Y. Takubo, H. Yamamoto

FPCCD ILC vertex detector

■ ILC(International Linear Collider)

- precision measurement of Higgs couplings
- High efficiency, purity flavor tagging

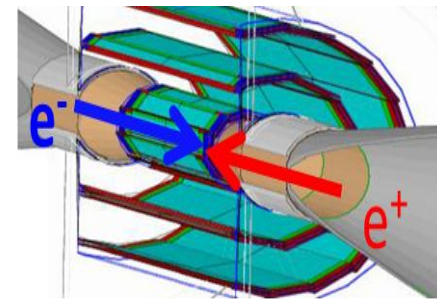
➤ Need high impact parameter resolution



■ vertex detector

- High impact para. resolution  near IP
- Accurate tracking  pixel occupancy~1%

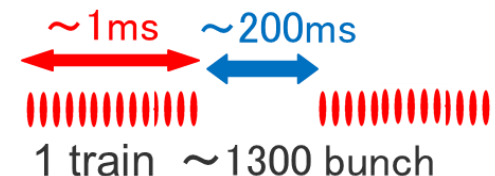
➤ Finely segmented pixel



■ FPCCD(FinePixelCCD) vertex detector

- Pixel size $5 \times 5 \mu\text{m}^2$: 😊 high position resolution, 😞 faint signal
- total # pix: 1.6×10^{10} : 😞 high speed readout
- Fully depleted epi-layer : $15 \mu\text{m}$, Si total $50 \mu\text{m}$: 😊 high 2 track separation capability
- inter-train time readout: 😊 free from beam induced RF noise

➤ Develop Readout ASIC for FPCCD



Requirements for FPCCD readout ASIC

■ readout speed > 10Mpix/sec

- 6000 ch parallel readout of
- all pixels within inter-train time(200ms)

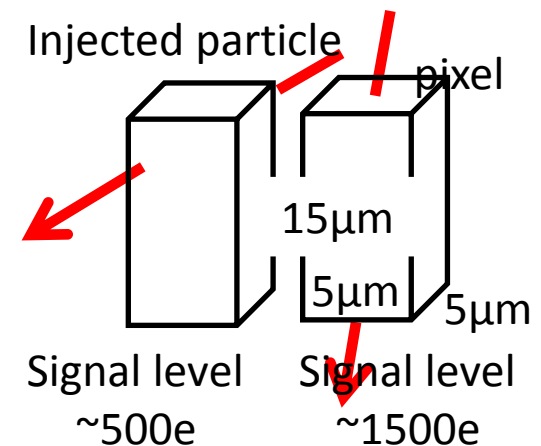
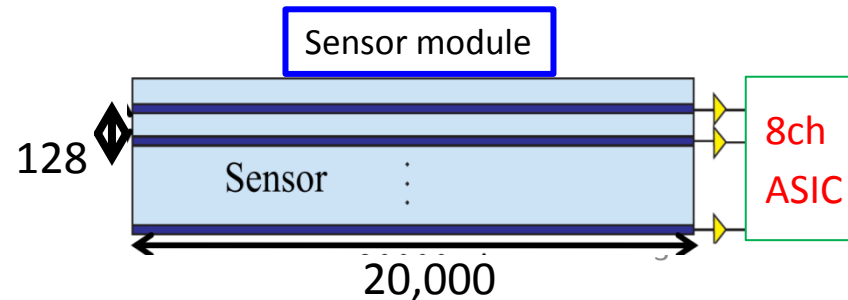
■ signal meas. accuracy < 30 e-

- Faint signal level : ~500 e-
- Noise + AD conversion accuracy < 30 e-

■ power consumption < 6mW/ch (ASIC) < 10mW/ch (CCD)

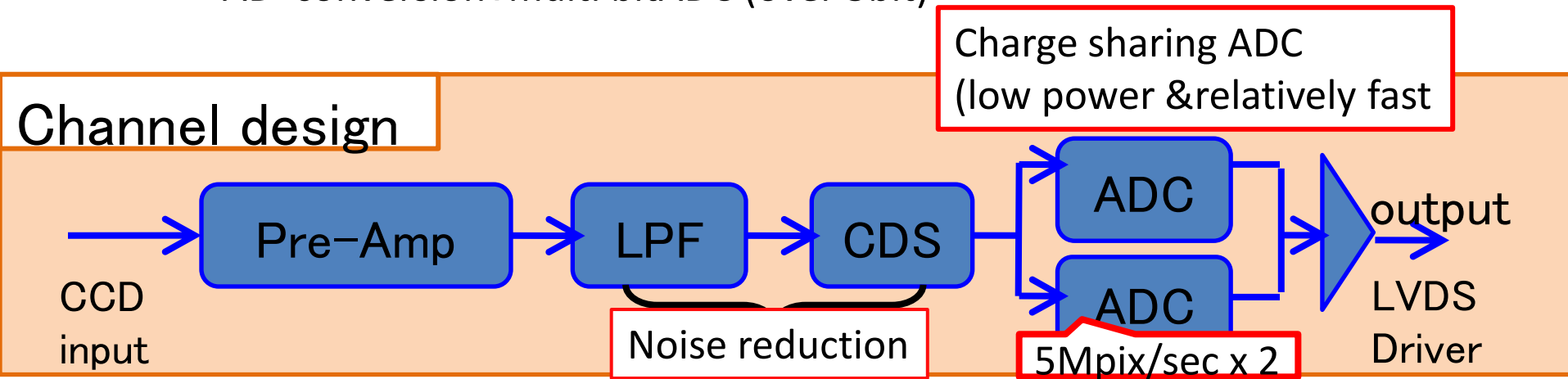
- Placed in -40°C cryostat

➤ **Develop readout ASIC that satisfies all requirements**



Overall ASIC design

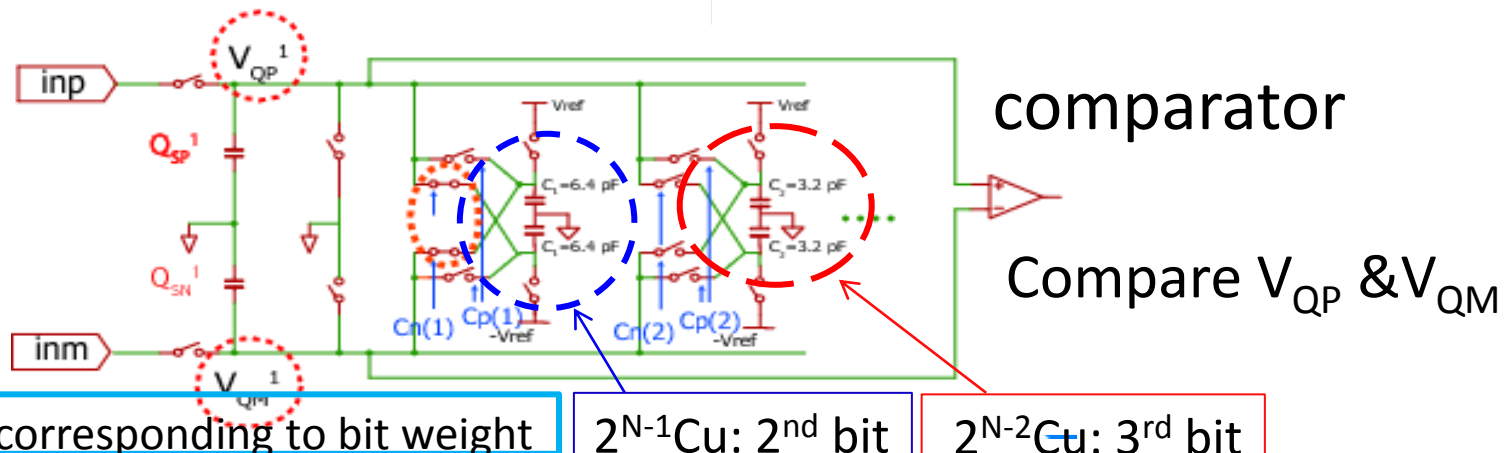
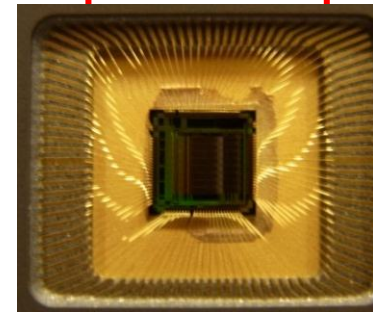
- Power consumption <6mW/ch
 - Main power source is ADC
 - Implement charge sharing ADC
- Readout speed >10 M pixel/s
 - Use two 5Mpixel/s parallelly
- Meas. accuracy of CCD signal <30 e-
 - Noise: implement LPF & Correlated double sampling (CDS).
 - AD conversion: multi bitADC (over 5bit)



FPCCD2B prototype design 1

- FPCCD2B(2nd prototype ASIC)
 - For Readout speed and meas. accuracy requirements
 - 0.35umTSMC process, 8 ch
 - Chip size : 4.3mm × 4.3mm
- SAR ADC design
 - 8 bit signal
 - 8 consecutive capacitor blocks for charge sharing

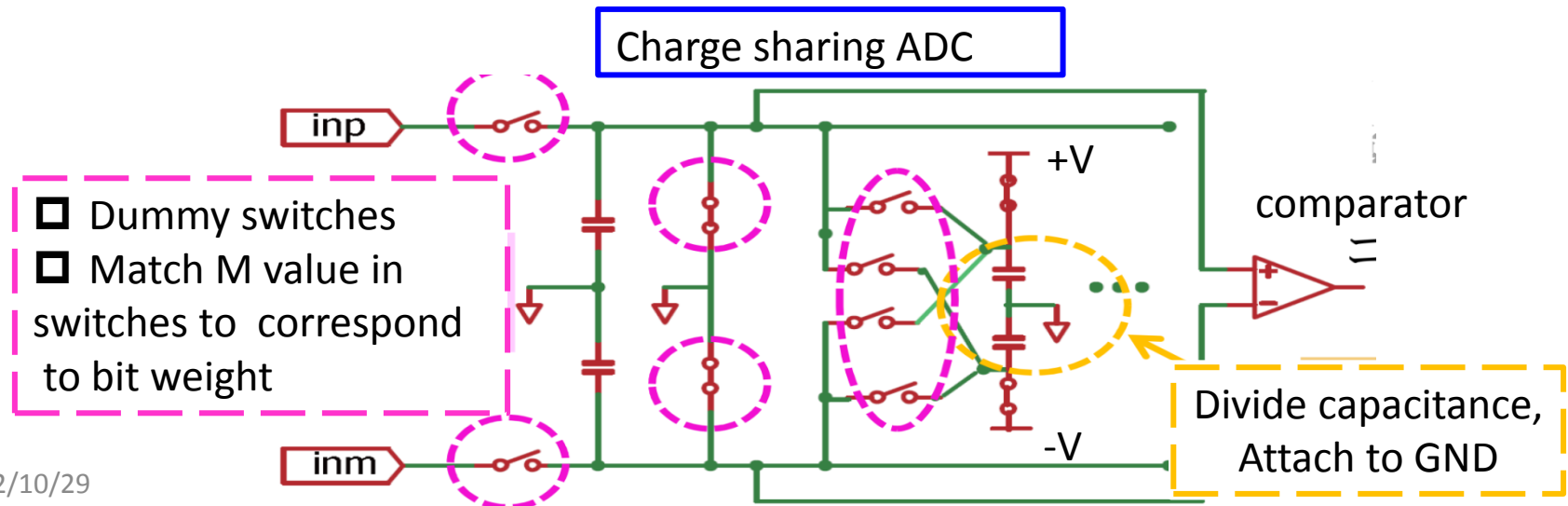
FPCCD2B



FPCCD2B prototype design 2

■ High speed and precision measurements

- Suppress the effect of stray capacitance attached to switches and in between GND.
- Increase current supply to ADC comparator by increasing # of pins 80→100



FPCCD2B results

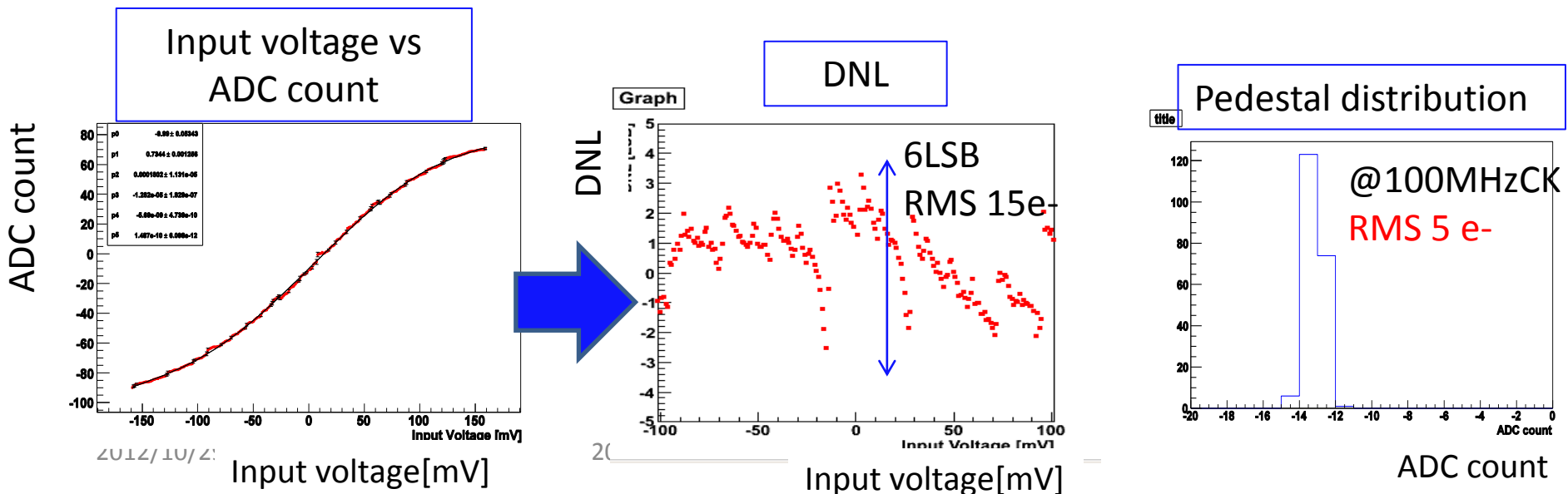
■ Power consumption

- 30.8mW/ch (>6mW/ch)→improved in next prototype

■ $meas. accuracy = \sqrt{DNL^2 + pedestal width^2}$

- $meas. accuracy@100MHzCK = \sim 16 e^-$

< 30 e⁻ required



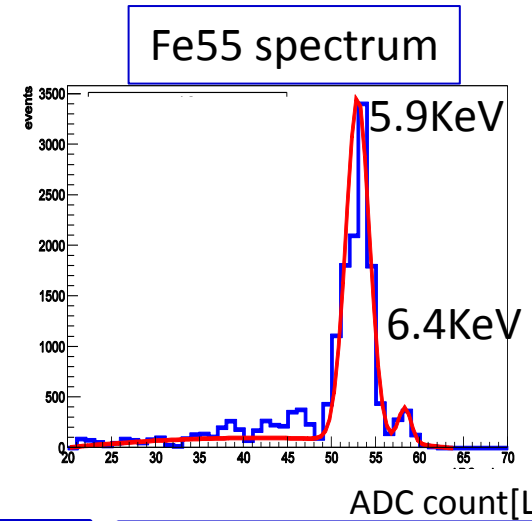
FPCCD2B results with CCD

■ CCD (Manufactured by Hamamatsu Photonics)

- 12x12 μm^2 two phase CCD
- thickness: epi layer 15 μm , Si total 50 μm

■ Fe55

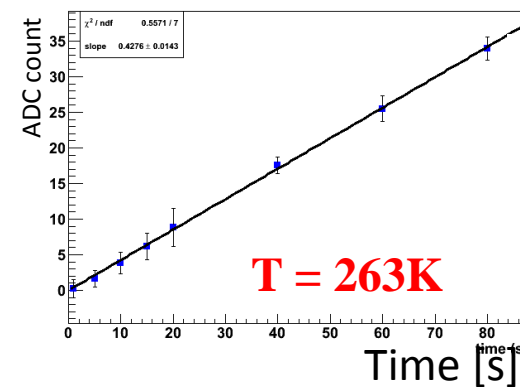
- irradiation time 10s, -40°C, 3000 frames
- S/N : 37 (Single pixel hit ext)
- energy resolution: 120 eV



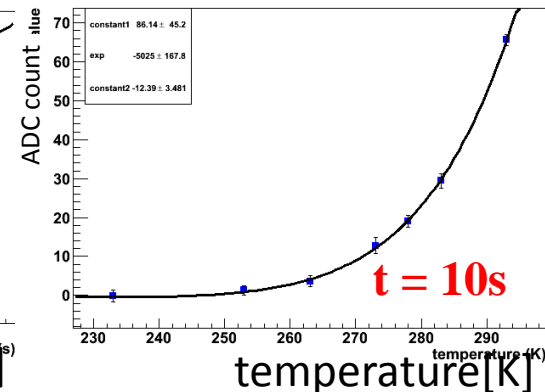
■ Pedestal analysis

- Dark current suppressed under ILC conditions (200ms -40°C)
- Noise $\sim 55 e^-$
(CCD readout main source)

Dark cu Time dependence



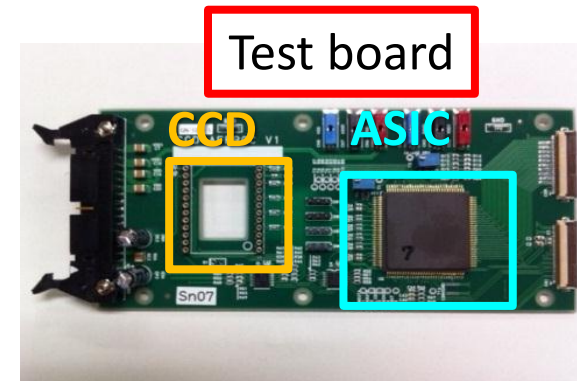
Temperature dependence



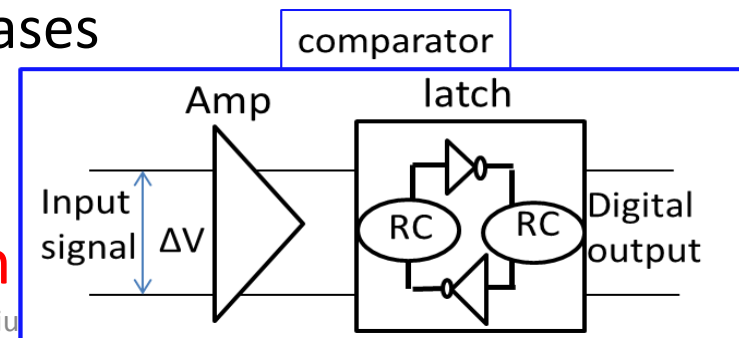
➤ FPCCD2B overall satisfies all requirements except power consumption

AFFROC01 design

- AFFROC01(3rd prototype ASIC)
 - Low power consuming prototype
 - TSMC CMOS process 0.25 μ m
 - Chip parameter 3.7x3.75mm²
- Power consumption modifications
 - Circuit simplification
 - Substitute with more energy conserving circuit
 - Process modification (0.35 \rightarrow 0.25 μ m)
- Modifications due to process modification
 - Comparator operation speed increases
 - Enable comparator speed control and improve DNL

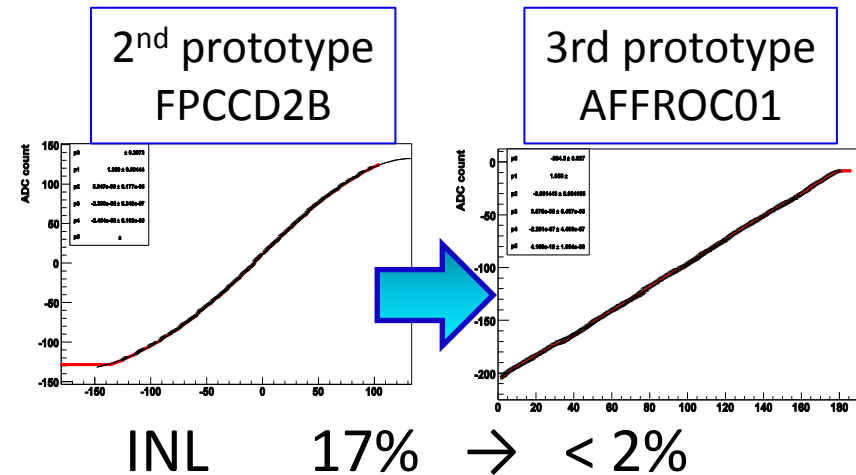


➤ Succeeded in 100MHz CK operation

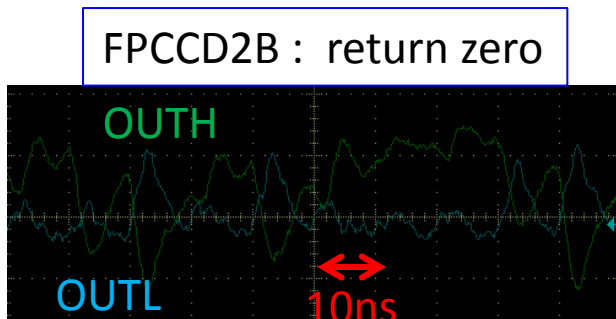


AFFROC01 improvement results

- INL(integral non linearity)
 - Shows curvature in linearity.
 - Caused upstream circuits.

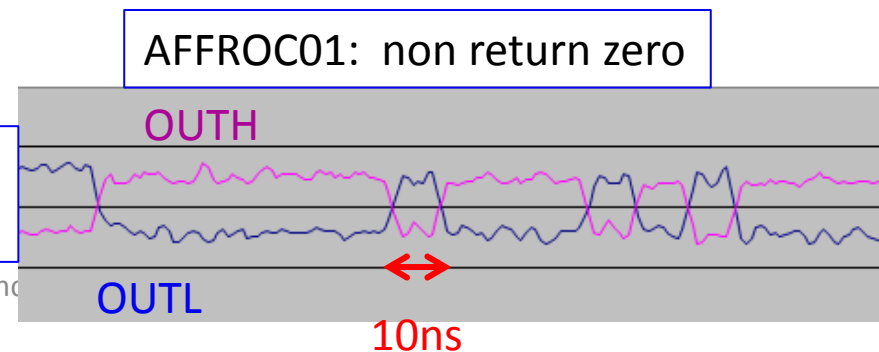


- baseband transmission
 - 10Mpix/s = 100MHz ADC comparator CK
 - Return zero → non return zero
 - Longer high period(10ns), Easy sampling



Measured LVDS
output signal

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AFFROC01 DNL improvement

<FPCCD2B>

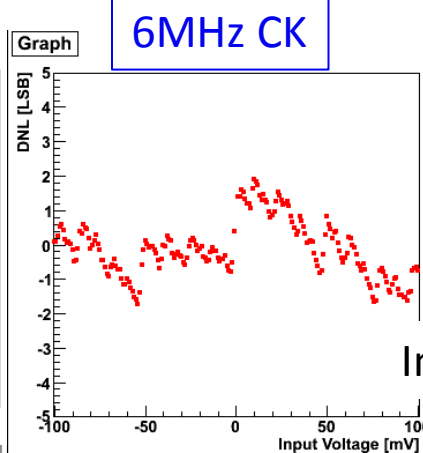
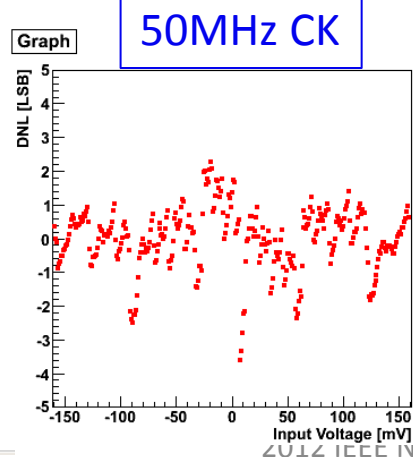
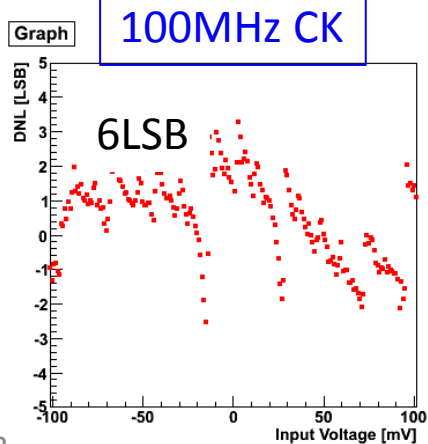
- DNL @ low frequency
 - capacitance ratio in SAR ADC capacitor displaced from bit weight
- DNL @ high frequency (100MHz CK)
 - meta-stable state @ bit change. Thus causes bit jump @high freq.
- Process change + Speed control @3rd prototype

<AFFROC01>

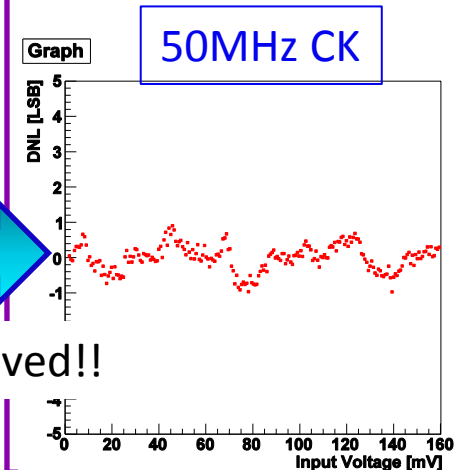
- Improvement seen

FPCCD2B (2nd prototype)

AFFROC01 3rd prototype



Improved!!



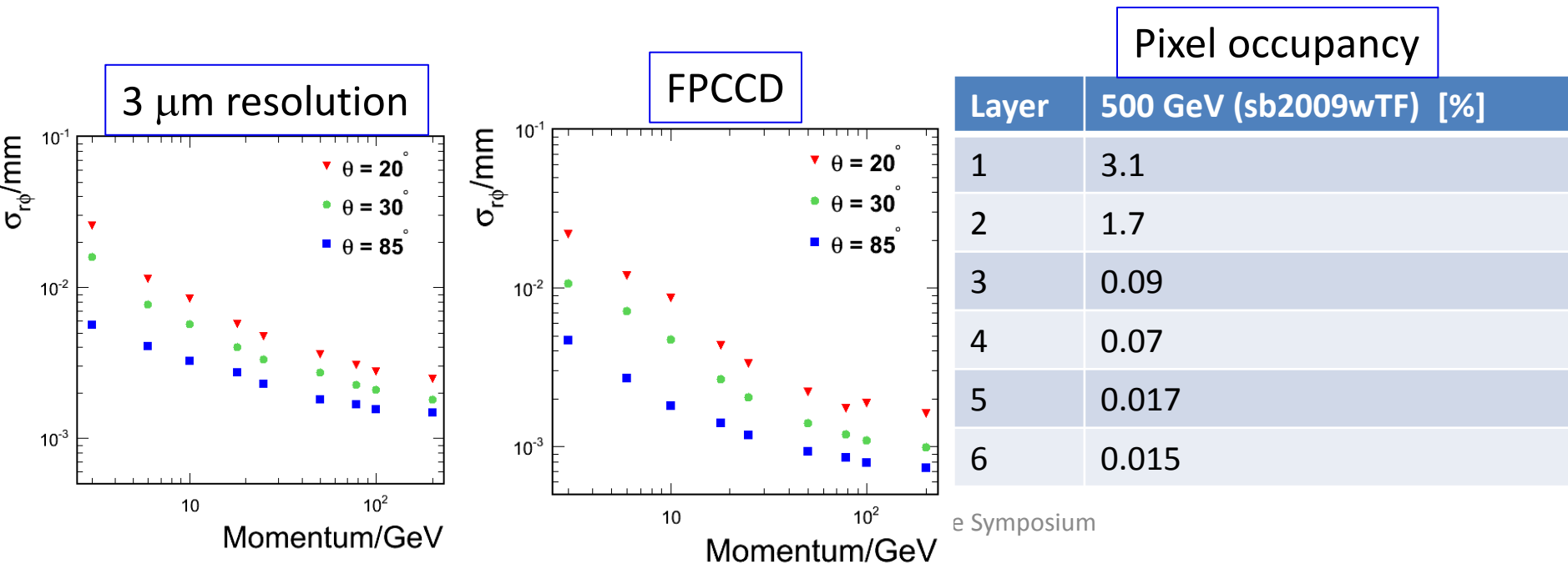
Summary

- FPCCD2B ASIC (2nd prototype)
 - Power consumption 30.8 mW/ch
 - Measurement accuracy 16 e- @100MHzCK
 - 55 e- when attached to 12 μ m² CCD
 - Able to operate detailed CCD evaluation tests.
- FPCCD2B overall satisfies all requirements except for power consumption.
- AFFROC01 (3rd prototype) is working@100MHz CK
 - Improved Power consumption of 4.8mW/ch
 - As well as meas. accuracy and other improvements(INL, LVDS signal, DICEFF radiation tolerance)

BACKUP

FPCCD impact parameter resolution¹⁴ & pixel occupancy

- FPCCD can improve the Impact Parameter resolution.
 - Significant improvement in high momentum region



Charge sharing ADC

■ Charge sharing ADC

- Compare standard 0 level & input charge(modified after determining every bit)
- Determine to subtract or add stored charge(charge sharing)
- There are 8 types of stored charge, each are binary weighted.
(binary search)

■ Low power consumption

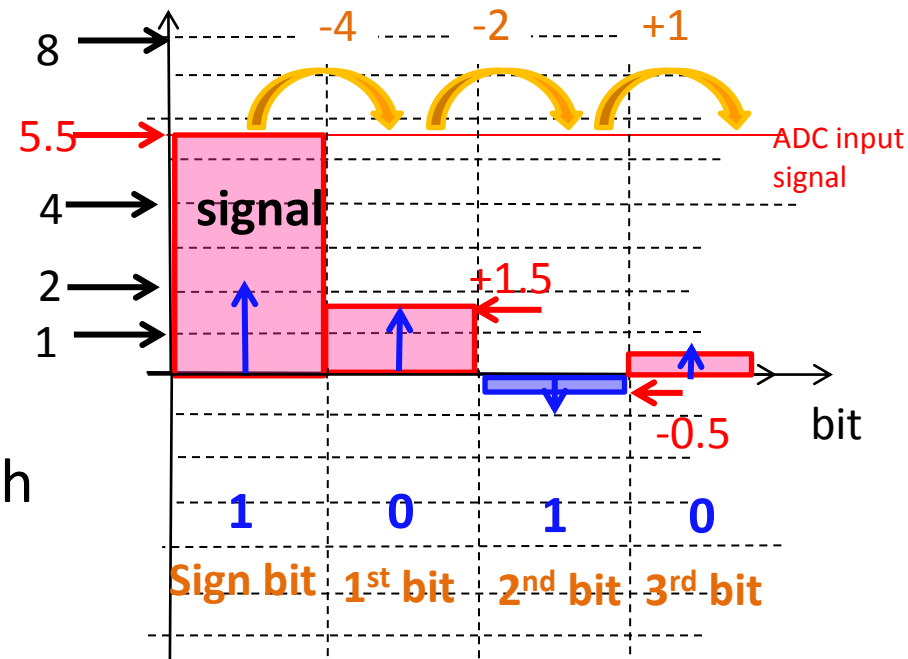
- SAR → one comparator

■ High accuracy

- Binary search

■ Readout speed

- Relatively high speed enough for requirement



FPCCD2B frequency dependence

■ Detailed frequency dependency

@ low frequency

- SAR ADC capacitor, capacitance ratio displacement from bit weight

@ high frequency (100MHz CK)

- meta-stable state @ bit change. causes bit jump @high freq.

